

ISO7421A-Q1 SLLSE14B – MARCH 2012 – REVISED SEPTEMBER 2013

LOW-POWER DUAL DIGITAL ISOLATORS

# FEATURES

- Qualified for Automotive Applications
- AEC-Q100 Qualified With the Following Results:
  - Device Temperature Grade 1: –40°C to 125°C Ambient Operating Temperature Range
  - Device HBM ESD Classification Level H3A
  - Device CDM ESD Classification Level C5
- High Signaling Rate: 50 Mbps
- Low Power Consumption
- Low Propagation Delay 9 ns (Typical)
- Low Skew 300 ps (Typical)
- 4-kVpeak Maximum Isolation, 2.5 kVrms per UL 1577, IEC/VDE and CSA Approved, IEC 60950-1, IEC 61010-1 End Equipment Standards Approved. All Approvals Pending.
- 50 kV/µs Transient Immunity (Typical)
- Over 25-Year Isolation Integrity at Rated Voltage
- Operates From 3-V to 5.5-V Supply and Logic Levels

# DESCRIPTION

The ISO7421A-Q1 provides galvanic isolation up to 2.5 kVrms for 1 minute per UL. This digital isolator has two isolated channels with bidirectional channel configuration. Each isolation channel has a logic input and output buffer separated by a silicon dioxide ( $SiO_2$ ) insulation barrier. Used in conjunction with isolated power supplies, these devices prevent noise currents on a data bus or other circuit from entering the local ground and interfering with or damaging sensitive circuitry.

The devices have TTL input thresholds and require two supply voltages from 3 V to 5.5 V, or any combination. All inputs are 5-V tolerant when supplied from a 3-V supply.

#### ORDERING INFORMATION<sup>(1)</sup>

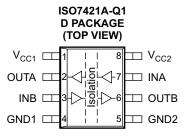
T <sub>A</sub>	PACK	AGE <sup>(2)</sup>	ORDERABLE PART NUMBER	TOP-SIDE MARKING
–40°C to 125°C	SOIC – D	Reel of 2500	ISO7421AQDRQ1	7421AQ

(1) For the most-current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI Web site at www.ti.com.

(2) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### **PIN FUNCTIONS**

P	PIN		PIN		DESCRIPTION
NAME	NO.	I/O	DESCRIPTION		
GND1	4	-	Ground connection for V <sub>CC1</sub>		
GND2	5	-	Ground connection for V <sub>CC2</sub>		
INA	7	I	Input, channel A		
INB	3	I	Input, channel B		
OUTA	2	0	Output, channel A		
OUTB	6	0	Output, channel B		
V <sub>CC1</sub>	1	-	Power supply, V <sub>CC1</sub>		
V <sub>CC2</sub>	8	-	Power supply, V <sub>CC2</sub>		

#### Table 1. FUNCTION TABLE<sup>(1)</sup>

INPUT SIDE VCC	OUTPUT SIDE VCC	INPUT IN	OUTPUT OUT
		Н	Н
PU	PU	L	L
		Open	Н
PD	PU	Х	Н

(1) PU = Powered up ( $V_{CC} \ge 3 V$ ), PD = Powered down ( $V_{CC} \le 2.4 V$ ), X = Irrelevant, H = High level, L = Low level

#### ABSOLUTE MAXIMUM RATINGS<sup>(1)</sup>

V <sub>CC</sub>	Supply voltage	<sup>(2)</sup> , V <sub>CC1</sub> , V <sub>CC2</sub>		–0.5 V to 6 V		
VI						
lo	I <sub>O</sub> Output current					
	Electrostatic discharge	Human-body model (HBM) AEC-Q100 Classification Level H3A		4 kV		
ESD		Charged-device model (CDM) AEC-Q100 Classification Level C5	All pins	1.5 kV		
	diseriarge	Machine model (MM)		200 V		
T <sub>J(Max)</sub>	Maximum junct	150°C				

(1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values except differential I/O bus voltages are with respect to network ground terminal and are peak voltage values.

## **RECOMMENDED OPERATING CONDITIONS**

		MIN	TYP	MAX	UNIT
$V_{CC1}, V_{CC2}$	Supply voltage	3		5.5	V
I <sub>OH</sub>	High-level output current	-4			mA
I <sub>OL</sub>	Low-level output current			4	mA
V <sub>IH</sub>	High-level input voltage	2		$V_{CC}$	V
VIL	Low-level input voltage	0		0.8	V
T <sub>A</sub>	Operating temperature	-40		125	°C





# **ELECTRICAL CHARACTERISTICS**

 $V_{CC1} = V_{CC2} = 5 \text{ V} \pm 10\%$ ,  $T_A = -40^{\circ}\text{C}$  to  $125^{\circ}\text{C}$ 

	PARAMETER			TEST CONDITIONS	MIN	TYP	MAX	UNIT
V			I <sub>OH</sub> =	= –4 mA, see Figure 1	V <sub>CC</sub> - 0.8	4.6		V
V <sub>OL</sub> Lc           V <sub>I(HYS)</sub> In           I <sub>IH</sub> Hi           I <sub>IL</sub> Lc           C <sub>1</sub> In           CMTI         Cd           SUPPLY C         Icc1           Icc2         Icc1           Icc2         Icc1	High-level output voltage		I <sub>OH</sub> =	= –20 μA, see Figure 1	V <sub>CC</sub> – 0.1	5		V
$\begin{array}{c c} V_{OH} & H \\ \hline V_{OL} & L \\ \hline V_{I(HYS)} & Ir \\ \hline I_{IH} & H \\ \hline I_{IL} & L \\ \hline C_{I} & Ir \\ \hline CMTI & C \\ \hline SUPPLY \\ \hline I_{CC1} \\ \hline I_{CC2} \\ \hline I_{CC1} \\ \hline I_{CC2} \\ \hline S \\ $			I <sub>OL</sub> =	4 mA, see Figure 1		0.2	0.4	V
VOL	Low-level output voltage	Ic Ic Ic Ic Ic Ic Ic Ic Ic Ic	I <sub>OL</sub> =	= 20 μA, see Figure 1		0	0.1	v
V <sub>I(HYS)</sub>	Input threshold voltage hysteresis					400		mV
I <sub>IH</sub>	High-level input current		$I_{OH} = -$ $I_{OL} = 2$ $I_{$	om 0 V or V <sub>CC</sub>			10	μA
IIL	Low-level input current				-10			μA
CI	Input capacitance to ground		IN at $V_{CC}$ , $V_I = 0.4 \sin (4E6\pi t)$			1.2		pF
CMTI	Common-mode transient immunity		$V_1 = V_{CC}$ or 0 V, see Figure 3		25	50		kV/µs
SUPPL	Y CURRENT (All inputs switching	with square	wave	clock signal for dynamic I <sub>CC</sub> meas	urement)			
I <sub>CC1</sub>		DC to 1 Mb	00	DC Input: $V_I = V_{CC}$ or 0 V		2.3	3.6	
I <sub>CC2</sub>		DC tO T MD	μs	AC Input: $C_L = 15 \text{ pF}$		2.3	3.6	
I <sub>CC1</sub>		10 Mbpo				2.9	4.5	
I <sub>CC2</sub>	Supply current for $V_{CC1}$ and $V_{CC2}$					2.9	4.5	mA
I <sub>CC1</sub>	Supply current for V <sub>CC1</sub> and V <sub>CC2</sub>	25 Mbpc		C <sub>L</sub> = 15 pF		4.3	6	ШA
I <sub>CC2</sub>						4.3	6	
I <sub>CC1</sub>	50 Mbra					6	9.1	
I <sub>CC2</sub>		20 Minha				6	9.1	

# SWITCHING CHARACTERISTICS

 $V_{CC1}$  =  $V_{CC2}$  = 5 V ±10%,  $T_A$  = –40°C to 125°C

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation delay time	See Figure 1		9	14	ns
PWD <sup>(1)</sup>	Pulse duration distortion  t <sub>PHL</sub> – t <sub>PLH</sub>			0.3	3.7	ns
t <sub>sk(pp)</sub>	Part-to-part skew time				4.9	ns
t <sub>sk(o)</sub>	Channel-to-channel output skew time				3.6	ns
t <sub>r</sub>	Output signal rise time	See Figure 1		1		ns
t <sub>f</sub>	Output signal fall time			1		ns
t <sub>fs</sub>	Fail-safe output delay time from input power loss	See Figure 2		6		μs
t <sub>ui</sub>	Input pulse duration		7			ns
1 / t <sub>ui</sub>	Signaling rate		0		50	Mbps

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# **ELECTRICAL CHARACTERISTICS**

 $V_{CC1} = 5 \text{ V} \pm 10\%$ ,  $V_{CC2} = 3.3 \text{ V} \pm 10\%$ ,  $T_A = -40^{\circ}\text{C}$  to  $125^{\circ}\text{C}$ 

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V		I <sub>OH</sub> = -4	I <sub>OH</sub> = -4 mA, see Figure 1, 5-V side				V
V <sub>OL</sub> L V <sub>I(HYS)</sub> II I <sub>IH</sub> F I <sub>IL</sub> L C <sub>I</sub> II CMTI C SUPPLY I <sub>CC1</sub> I <sub>CC2</sub> I <sub>CC1</sub> I <sub>CC2</sub>	High-level output voltage	$I_{OH} = -20$	μA, see Figure 1	V <sub>CC</sub> - 0.1			v
V		I <sub>OL</sub> = 4 m	A, see Figure 1			0.4	V
VOL	Low-level output voltage	I <sub>OL</sub> = 20	JA, see Figure 1				v
V <sub>I(HYS)</sub>	Input threshold voltage hysteresis				400		mV
I <sub>IH</sub>	High-level input current	IN from C	V or V			10	μA
IIL	Low-level input current		V or V <sub>CC</sub>	-10			μA
CI	Input capacitance to ground	IN at V <sub>CC</sub>	N at $V_{CC}$ , $V_{I} = 0.4 \sin (4E6\pi t)$		1.2		pF
CMTI	Common-mode transient immunity	$V_I = V_{CC}$	or 0 V, see Figure 3	25	40		kV/µs
SUPPL	Y CURRENT (All inputs switching w	ith square wav	e clock signal for dynamic I <sub>CC</sub> mea	asurement)			
I <sub>CC1</sub>		DC to 1 Mbp	DC Input: $V_1 = V_{CC}$ or 0 V		2.3	3.6	
I <sub>CC2</sub>		DC to 1 Mbps	AC Input: $C_L = 15 \text{ pF}$		1.8	2.8	
I <sub>CC1</sub>		10 Mhno			2.9	4.5	
I <sub>CC2</sub>	Supply surrent for \/ and \/	10 Mbps			2.2	3.2	A
I <sub>CC1</sub>	Supply current for $V_{CC1}$ and $V_{CC2}$	OF Mhno	0 15 pF		4.3	6	mA
I <sub>CC2</sub>		25 Mbps	C <sub>L</sub> = 15 pF		2.8	4.1	
I <sub>CC1</sub>		50 Mbpo			6	9.1	
I <sub>CC2</sub>		50 Mbps			3.8	5.8	

# SWITCHING CHARACTERISTICS

 $V_{CC1}$  = 5 V ±10%,  $V_{CC2}$  = 3.3 V ±10%,  $T_A$  = –40°C to 125°C

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation delay time	See Figure 1		10	17	ns
PWD <sup>(1)</sup>	Pulse duration distortion  t <sub>PHL</sub> – t <sub>PLH</sub>			0.5	5.6	ns
t <sub>sk(pp)</sub>	Part-to-part skew time				6.3	ns
t <sub>sk(o)</sub>	Channel-to-channel output skew time				4	ns
t <sub>r</sub>	Output signal rise time	See Figure 1		2		ns
t <sub>f</sub>	Output signal fall time			2		ns
t <sub>fs</sub>	Fail-safe output delay time from input power loss	See Figure 2		6		μs
t <sub>ui</sub>	Input pulse duration		7			ns
1 / t <sub>ui</sub>	Signaling rate		0		50	Mbps



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## ELECTRICAL CHARACTERISTICS

 $V_{CC1} = 3.3 \text{ V} \pm 10\%$ ,  $V_{CC2} = 5 \text{ V} \pm 10\%$ ,  $T_A = -40^{\circ}\text{C}$  to  $125^{\circ}\text{C}$ 

	PARAMETER	Т	EST CONDITIONS	MIN	TYP	MAX	UNIT
\ <i>\</i>		I <sub>OH</sub> = -4 mA, s	ee Figure 1, 3.3-V side	$V_{CC} - 0.4$			V
V <sub>OH</sub>	High-level output voltage	I <sub>OH</sub> = -20 μA, s	$OH = -4 \text{ mA}$ , see Figure 1, 3.3-V side $V_{CC} - 0.4$ $OH = -20 \ \mu\text{A}$ , see Figure 1 $V_{CC} - 0.1$ $OL = 4 \text{ mA}$ , see Figure 1       0 $OL = 20 \ \mu\text{A}$ , see Figure 1       0 $OL = 20 \ \mu\text{A}$ , see Figure 1       0 $OL = 20 \ \mu\text{A}$ , see Figure 1       0 $OL = 20 \ \mu\text{A}$ , see Figure 1       0 $OL = 20 \ \mu\text{A}$ , see Figure 1       0 $OL = 20 \ \mu\text{A}$ , see Figure 1       0 $OL = 20 \ \mu\text{A}$ , see Figure 1       0 $OL = 20 \ \mu\text{A}$ , see Figure 1       0 $OL = 20 \ \mu\text{A}$ , see Figure 1       0 $V_{CC} = 0.1$ -10         N from 0 V or $V_{CC}$ -10         N at $V_{CC}$ , $V_I = 0.4 \ sin (4E6 \pi t)$ 1 $V_I = V_{CC}$ or 0 V, see Figure 3       25         are wave clock signal for dynamic $I_{CC}$ measurement)		v		
V		I <sub>OL</sub> = 4 mA, see	e Figure 1		$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	0.4	V
V <sub>OL</sub>	Low-level output voltage	I <sub>OL</sub> = 20 μA, se	e Figure 1		0		v
V <sub>I(HYS)</sub>	Input threshold voltage hysteresis				400		mV
I <sub>IH</sub>	High-level input current	IN from 0 V/ or	$I_{OH} = -4 \text{ mA, see Figure 1, 3.3-V side}$ $I_{OH} = -20 \ \mu\text{A, see Figure 1}$ $I_{OL} = 4 \text{ mA, see Figure 1}$ $I_{OL} = 20 \ \mu\text{A, see Figure 1}$ $I_{OL} = 20 \ \mu\text{A, see Figure 1}$ $IN \ from 0 \ V \ or \ V_{CC}$ $IN \ at \ V_{CC}, \ V_{I} = 0.4 \ sin \ (4E6\pi t)$ $V_{I} = V_{CC} \ or \ 0 \ V, see \ Figure 3$ are wave clock signal for dynamic I <sub>CC</sub> measure $IC \ 1 \ Mbps$ $DC \ Input: \ V_{I} = V_{CC} \ or \ 0 \ V \ AC \ Input: \ C_{L} = 15 \ pF$			10	μA
IIL	Low-level input current	$\begin{tabular}{ c c c c c } \hline I_{OH} &= -4 \text{ mA, see Figure} \\ \hline I_{OH} &= -20 \ \mu\text{A, see Figure} \\ \hline I_{OL} &= 4 \ \text{mA, see Figure} \\ \hline I_{OL} &= 20 \ \mu\text{A, see Figure} \\ \hline \hline IN \ from 0 \ V \ or \ V_{CC} \\ \hline IN \ at \ V_{CC}, \ V_I &= 0.4 \ sine \\ \hline V_I &= V_{CC} \ or \ 0 \ V, \ see Figure \\ \hline h \ square \ wave \ clock \ signed \\ \hline DC \ to \ 1 \ Mbps \\ \hline 10 \ Mbps \\ \hline \end{tabular}$	VCC	-10			μA
CI	Input capacitance to ground	IN at $V_{CC}$ , $V_{I}$ =	0.4 sin (4E6πt)		1		pF
CMTI	Common-mode transient immunity	$V_{I} = V_{CC} \text{ or } 0 V$	$V_{I} = V_{CC}$ or 0 V, see Figure 3		40		kV/µs
SUPPL	Y CURRENT (All inputs switching with	n square wave cloc	k signal for dynamic I <sub>CC</sub> meas	urement)			
I <sub>CC1</sub>		DC to 1 Mbps	DC Input: $V_I = V_{CC}$ or 0 V		1.8	2.8	
I <sub>CC2</sub>		DC to T Mbps	AC Input: $C_L = 15 \text{ pF}$		2.3	3.6	
I <sub>CC1</sub>		10 Mbpo			2.2	3.2	
I <sub>CC2</sub>	Supply ourrest for V and V				2.9	4.5	mA
I <sub>CC1</sub>	Supply current for $V_{CC1}$ and $V_{CC2}$	25 Mbpo	C = 15  pF		2.8	4.1	ma
I <sub>CC2</sub>		25 Mbps	$C_L = 10 \text{ pr}$		4.3	6	
I <sub>CC1</sub>		50 Mbps			3.8	5.8	
I <sub>CC2</sub>					6	9.1	

## SWITCHING CHARACTERISTICS

 $V_{CC1}$  = 3.3 V ±10%,  $V_{CC2}$  = 5 V ±10%,  $T_A$  = -40°C to 125°C

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation delay time	See Figure 1		10	17	ns
PWD <sup>(1)</sup>	Pulse duration distortion  t <sub>PHL</sub> – t <sub>PLH</sub>			0.5	4	ns
t <sub>sk(pp)</sub>	Part-to-part skew time				8.5	ns
t <sub>sk(o)</sub>	Channel-to-channel output skew time				4	ns
t <sub>r</sub>	Output signal rise time	See Figure 1		2		ns
t <sub>f</sub>	Output signal fall time			2		ns
t <sub>fs</sub>	Fail-safe output delay time from input power loss	See Figure 2		6		μs
t <sub>ui</sub>	Input pulse duration		7			ns
1 / t <sub>ui</sub>	Signaling rate		0		50	Mbps

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# **ELECTRICAL CHARACTERISTICS**

 $V_{CC1} = V_{CC2} = 3.3 \text{ V} \pm 5\%$ ,  $T_{A} = -40^{\circ}\text{C}$  to  $125^{\circ}\text{C}$ 

	PARAMETER	т	EST CONDITIONS	MIN	TYP	MAX	UNIT
V		I <sub>OH</sub> = -4 mA, se	ee Figure 1	$V_{CC} - 0.4$	3		V
V <sub>OH</sub>	High-level output voltage	I <sub>OH</sub> = -20 μA, s	ee Figure 1	V <sub>CC</sub> – 0.1	3 3.3 0.2 0 400 1 1 40 1.8 1.8 2.2 2.2 2.8 2.8 3.8		V
N/		I <sub>OL</sub> = 4 mA, see	e Figure 1		0.2	0.4	V
V <sub>OL</sub>	Low-level output voltage	I <sub>OL</sub> = 20 μA, se	e Figure 1		0		V
V <sub>I(HYS)</sub>	Input threshold voltage hysteresis				400		mV
IIH	High-level input current	IN from 0 1/ or	IN from 0 V or V <sub>CC</sub>			10	μA
IIL	Low-level input current		VCC	-10			μA
CI	Input capacitance to ground	IN at $V_{CC}$ , $V_I =$	IN at $V_{CC}$ , $V_I = 0.4 \sin (4E6\pi t)$		1		pF
CMTI	Common-mode transient immunity	$V_{I} = V_{CC} \text{ or } 0 V$	$V_{I} = V_{CC}$ or 0 V, see Figure 3.		40		kV/µs
SUPPL	Y CURRENT (All inputs switching with	h square wave cloc	k signal for dynamic I <sub>CC</sub> meas	urement)			
I <sub>CC1</sub>		DC to 1 Mbro	DC Input: $V_I = V_{CC}$ or 0 V		1.8	2.8	
I <sub>CC2</sub>		DC to 1 Mbps	AC Input: $C_L = 15 \text{ pF}$		1.8	2.8	
I <sub>CC1</sub>	*	10 Mhaa			2.2	3.2	
I <sub>CC2</sub>	Supply surrent for )(	10 Mbps			2.2	3.2	
I <sub>CC1</sub>	Supply current for $V_{CC1}$ and $V_{CC2}$	25 Mhno	0 15 55		2.8	4.1	mA
I <sub>CC2</sub>		25 Mbps	C <sub>L</sub> = 15 pF		2.8	4.1	
I <sub>CC1</sub>		EQ Mbaa			3.8	5.8	
I <sub>CC2</sub>		50 Mbps			3.8	5.8	

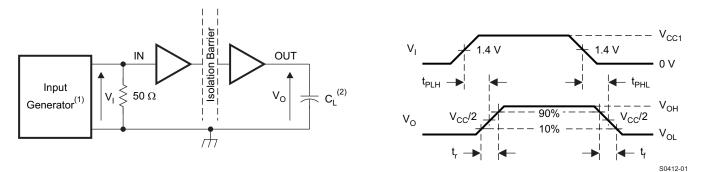
# SWITCHING CHARACTERISTICS

 $V_{CC1} = V_{CC2} = 3.3 \text{ V} \pm 5\%$ ,  $T_A = -40^{\circ}\text{C}$  to  $125^{\circ}\text{C}$ 

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation delay time	See Figure 1		12	20	ns
PWD <sup>(1)</sup>	Pulse duration distortion  t <sub>PHL</sub> – t <sub>PLH</sub>			1	5	ns
t <sub>sk(pp)</sub>	Part-to-part skew time				6.8	ns
t <sub>sk(o)</sub>	Channel-to-channel output skew time				5.5	ns
t <sub>r</sub>	Output signal rise time			2		ns
t <sub>f</sub>	Output signal fall time	See Figure 1		2		ns
t <sub>fs</sub>	Fail-safe output delay time from input power loss	See Figure 2		6		μs
t <sub>ui</sub>	Input pulse duration		7			ns
1 / t <sub>ui</sub>	Signaling rate		0		50	Mbps

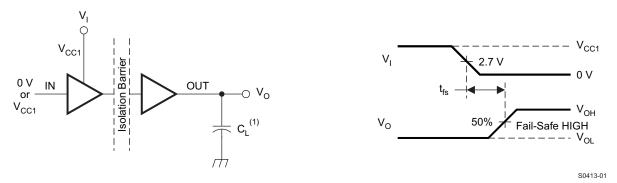


#### PARAMETER MEASUREMENT INFORMATION



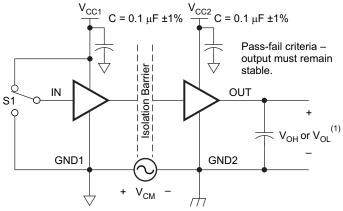
- (1) The input pulse is supplied by a generator having the following characteristics: PRR  $\leq$  50 kHz, 50% duty cycle,  $t_r \leq 3$  ns,  $t_f \leq 3$  ns,  $Z_O = 50 \Omega$ .
- (2)  $C_L = 15 \text{ pF}$  and includes instrumentation and fixture capacitance within ±20%.





(1)  $C_L = 15 \text{ pF}$  and includes instrumentation and fixture capacitance within ±20%.

#### Figure 2. Fail-Safe Output Delay-Time Test Circuit and Voltage Waveforms



S0414-01

(1)  $C_L = 15 \text{ pF}$  and includes instrumentation and fixture capacitance within ±20%.

#### Figure 3. Common-Mode Transient Immunity Test Circuit

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# **DEVICE INFORMATION**

# **PACKAGE CHARACTERISTICS**

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
L(I01)	Minimum air gap (clearance)	Shortest terminal-to-terminal distance through air	4.8			mm
L(102)	Minimum external tracking (creepage)	Shortest terminal-to-terminal distance across the package surface	4.3			mm
CTI	Tracking resistance (comparative tracking index)	DIN IEC 60112 / VDE 0303 Part 1	>175			V
	Minimum internal gap (internal clearance)	Distance through the insulation	0.008			mm
R <sub>IO</sub>	Isolation resistance	Input to output, $V_{IO}$ = 500 V, all pins on each side of the barrier tied together creating a two-terminal device, $T_A$ < 100°C		>10 <sup>12</sup>		Ω
		Input to output		>10 <sup>11</sup>		Ω
CIO	Barrier capacitance, input to output	$V_{I} = 0.4 \sin (4E6\pi t)$		1		pF

#### NOTE

Creepage and clearance requirements should be applied according to the specific equipment isolation standards of an application. Care should be taken to maintain the creepage and clearance distance of a board design to ensure that the mounting pads of the isolator on the printed-circuit board do not reduce this distance.

Creepage and clearance on a printed-circuit board become equal according to the measurement techniques shown in the Isolation Glossary. Techniques such as inserting grooves and/or ribs on a printed circuit board are used to help increase these specifications.

#### INSULATION CHARACTERISTICS<sup>(1)</sup>

over recommended operating conditions (unless otherwise noted)

	PARAMETER	SPECIFICATION	UNIT	
VIORM	Maximum working insulation voltage		560	V
V <sub>PR</sub>	Input-to-output test voltage	t = 1 s (100% production), partial discharge 5 pC	1050	V
N (	Transient energiet	t = 60 s (qualification)	4000	V
V <sub>IOTM</sub>	Transient overvoltage	t = 1 s (100% production)	4000	v
		t = 60 s (qualification)	2500	Marrie
V <sub>ISO</sub>	Isolation voltage per UL	t = 1 s (100% production)	3000	Vrms
R <sub>S</sub>	Insulation resistance	$V_{IO} = 500 \text{ V at } T_{S}$	>109	Ω
	Pollution degree		2	

(1) Climatic Classification 40/125/21

#### Table 2. IEC 60664-1 RATINGS TABLE

PARAMETER	TEST CONDITIONS	SPECIFICATION
Basic isolation group	Material group	III-a
	Rated mains voltage ≤ 150 Vrms	I–IV
Installation classification	Rated mains voltage ≤ 300 Vrms	I–III
	Rated mains voltage ≤ 400 Vrms	I—II



### **REGULATORY INFORMATION**

VDE	CSA	UL
Certified according to IEC 60747-5- 2	Approved under CSA Component Acceptance Notice	Recognized under 1577 Component Recognition Program <sup>(1)</sup>
File number: pending (40016131)	File number: pending (1698195)	File number: pending (E181974)

(1) Production tested  $\geq$  3000 Vrms for 1 second in accordance with UL 1577.

# LIFE EXPECTANCY versus WORKING VOLTAGE

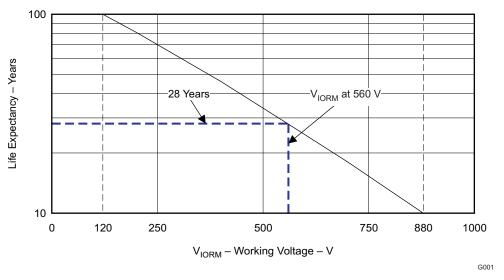


Figure 4. Life Expectancy versus Working Voltage

# **IEC SAFETY LIMITING VALUES**

Safety limiting intends to prevent potential damage to the isolation barrier upon failure of input or output circuitry. A failure of the I/O can allow low resistance to ground or the supply and, without current limiting, dissipate sufficient power to overheat the die and damage the isolation barrier, potentially leading to secondary system failures.

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
	Safety input, output, or supply	$\theta_{JA} = 212^{\circ}C/W, V_{I} = 5.5 V, T_{J} = 170^{\circ}C, T_{A} = 25^{\circ}C$			112	
IS	current	$\theta_{JA} = 212^{\circ}C/W, V_{I} = 3.6 V, T_{J} = 170^{\circ}C, T_{A} = 25^{\circ}C$			171	mA
Τ <sub>S</sub>	Maximum case temperature				150	°C

The safety-limiting constraint is the absolute-maximum junction temperature specified in the *Absolute Maximum Ratings* table. The power dissipation and junction-to-air thermal impedance of the device installed in the application hardware determines the junction temperature. The assumed junction-to-air thermal resistance in the *Thermal Characteristics* table is that of a device installed in the JESD51-3, Low-Effective-Thermal-Conductivity Test Board for Leaded Surface-Mount Packages and is conservative. The power is the recommended maximum input voltage times the current. The junction temperature is then the ambient temperature plus the power times the junction-to-air thermal resistance.

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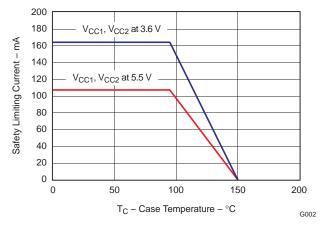
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# PACKAGE THERMAL CHARACTERISTICS

(over recommended operating conditions unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
θ <sub>JA</sub> Jun		Low-K thermal resistance <sup>(1)</sup>		212		0000
	Junction-to-air thermal resistance	High-K thermal resistance <sup>(1)</sup>	122		°C/W	
$\theta_{JB}$	Junction-to-board thermal resistance			37		°C/W
$\theta_{\text{JC}}$	Junction-to-case thermal resistance			69.1		°C/W
PD	Device power dissipation	$V_{CC1} = V_{CC2} = 5.5 \text{ V}, \text{ T}_{J} = 150^{\circ}\text{C}, \text{ C}_{L} = 15 \text{ pF},$ Input a 150-Mbps 50% duty-cycle square wave			390	mW

(1) Tested in accordance with the low-K or high-K thermal metric definitions of EIA/JESD51-3 for leaded surface mount packages





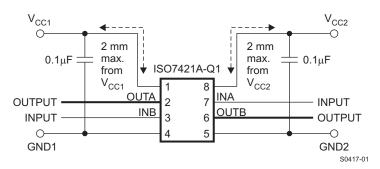


Figure 6. Typical ISO7421A-Q1 Application Circuit





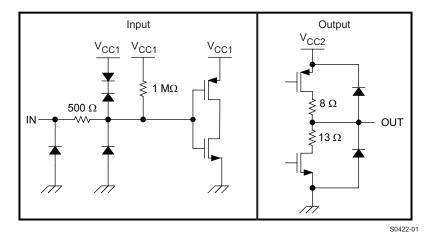
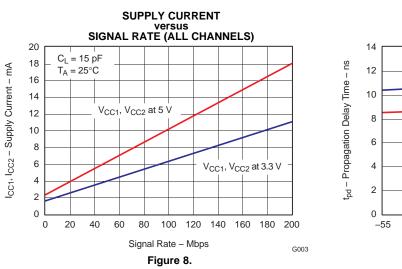
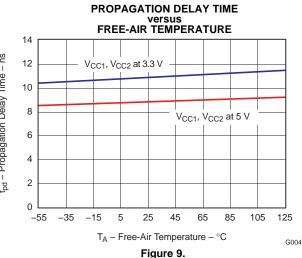
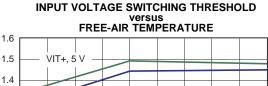


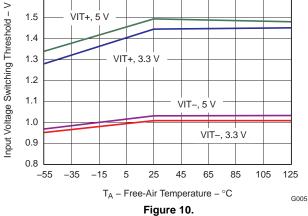
Figure 7. Device I/O Schematics

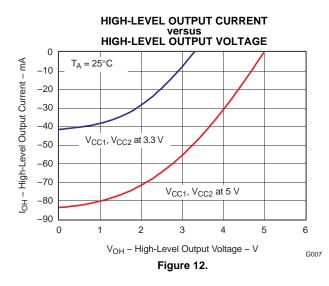


TYPICAL CHARACTERISTICS

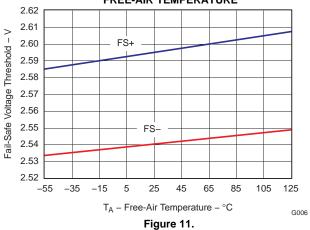


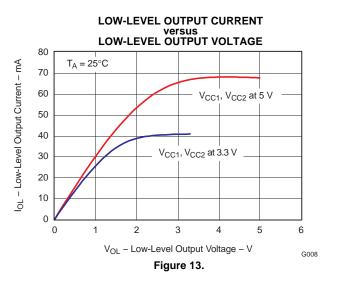






FAIL-SAFE VOLTAGE THRESHOLD versus FREE-AIR TEMPERATURE









ISO7421A-Q1 SLLSE14B – MARCH 2012 – REVISED SEPTEMBER 2013

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# **TYPICAL CHARACTERISTICS (continued)**

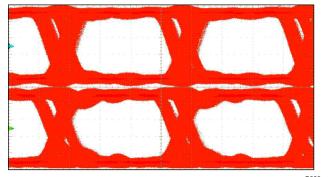


Figure 14. Eye Diagram at 250 MBPS, 5-V V<sub>CC</sub>, Typical

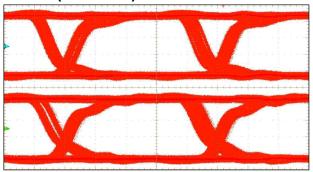


Figure 15. Eye Diagram at 200 MBPS, 5-V  $V_{CC},\,125^{\circ}\!\overset{_{G010}}{\text{C}}$ 

# **REVISION HISTORY**

#### Changes from Revision A (September 2012) to Revision B

•	Deleted ISO7420-Q1 part number from header of every page	. 1
•	Deleted ISO7420-Q1package from pinout drawing	. 1
•	Deleted ISO7420-Q1 part number from Description sectoin	. 1
•	Deleted ISO7420-Q1 from Ordering Information table	. 1
•	Deleted ISO7420-Q1 from Pin Functions table	. 2
•	Deleted ISO7420-Q1 from Supply Current section of 5-V, 5-V Electrical Characteristics table	. 3
•	Deleted ISO7420-Q1 from Supply Current section of 5-V, 3.3-V Electrical Characteristics table	. 4
•		. 5
•	Deleted ISO7420-Q1 from Supply Current section of 3.3-V, 5-V Electrical Characteristics table	. 5
•	Deleted ISO7420-Q1 from Supply Current section of 3.3-V, 5-V Electrical Characteristics table	. 6
•	Corrected part number in Typical Application Circuit diagram	10

#### Changes from Original (March, 2012) to Revision A

# Changed High Signaling Rate from 1 to 50 Mbps. 1 Replaced Supply Current section with marked up table from commercial datasheet SLLSE45, 8.5 max value changed to 9.1. 3 Changed Signaling rate max value from 1 to 50. 3 Replaced Supply Current section with marked up table from commercial datasheet SLLSE45, 8.5 max value changed to 9.1 and 5.5 changed to 5.8. 4 Changed Signaling rate from 1 to 50 Mbps. 4 Replaced Supply Current section with marked up table from commercial datasheet SLLSE45, 5.5 max value changed to 5.8 and 8.5 changed to 9.1. 5 Changed Signaling rate from 1 to 50 Mbps. 5 Replaced Supply Current section with marked up table from commercial datasheet SLLSE45, 5.5 max value changed to 5.8 and 8.5 changed to 9.1. 5 Changed Signaling rate from 1 to 50 Mbps. 5 Replaced Supply Current section with marked up table from commercial datasheet SLLSE45, 5.5 max value changed to 5.8. 5 Changed Signaling rate from 1 to 50 Mbps. 5 Replaced Supply Current section with marked up table from commercial datasheet SLLSE45, 5.5 max value changed to 5.8. 6 Changed Signaling rate from 1 to 50 Mbps. 6 Changed Signaling rate from 1 to 50 Mbps. 6

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12-Sep-2013

# PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)		(3)		(4/5)	
ISO7421AQDRQ1	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 125	7421AQ	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

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# PACKAGE MATERIALS INFORMATION

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# TAPE AND REEL INFORMATION





# QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ISO7421AQDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

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# PACKAGE MATERIALS INFORMATION

13-Feb-2016



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ISO7421AQDRQ1	SOIC	D	8	2500	367.0	367.0	38.0

D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.





NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
   E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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